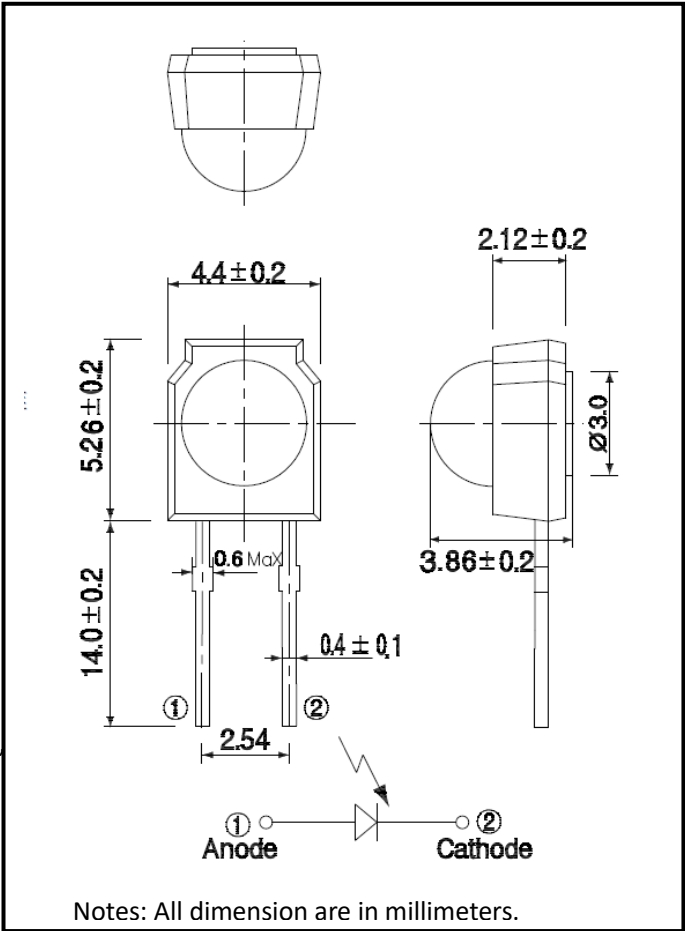
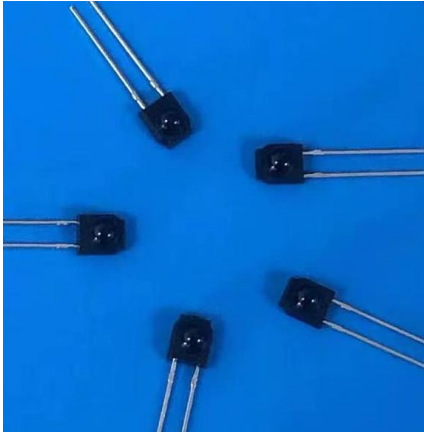


Silicon photodiode

OSD4-IPF



Description

The OSD4-IPF is IR response high-output, high-speed silicon Photo diode which is mounted in sidelooking molding package. Permits wide angular response.

Applications

- *Optical switch
- * Remote control sensors

Absolute Maximum Ratings (Ta=23°C)



Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	size	-	2.25*2.25			mm ²
Active area	A	-	2.0*2.0			mm ²
Dark current	I _D	V _R =100mV		15		pA
		V _R =10V			30000	
Turn on time/Turn off time	t _R	V _R =10V; R _L =1kΩ		50		ns
Tempcoeffi-cient of I _D	T _{CID}			0.18		times/°C
Reverse breakdown voltage	V _{(BR)R}	I _R =100uA E _v =0mw/cm ²	35			V
Junction Capacitance	C _J	V _R =0V f=1MHz E _e =0mW/cm ²		60		pF
		V _R =3V f=1MHz E _e =0mW/cm ²		27		
Photo sensitivity	S _R	650nm		0.38		A/W
Spectral Application Range	λ _{range}		800		1100	nm
Spectral Response-Peak	λ _p			940		nm
Forward Voltage	V _F	I _F =10mA, E _v =0mw/cm ²	0.5		1.3	V
Angular Resp 50% Resp Pt	θ ^{1/2}			±35		Degrees

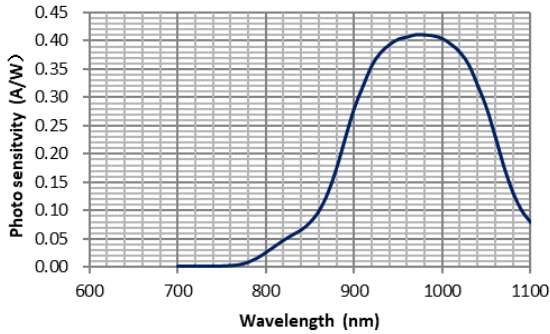
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OTRON ELECTRONIC TECHNOLOGY CO., LTD.

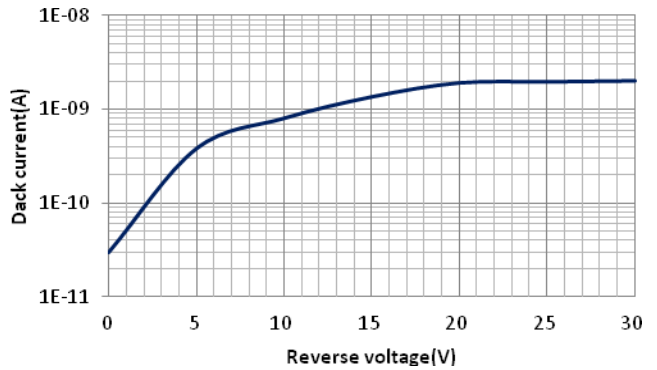
TEL:+86-21-54971821
 FAX:+86-21-54971823

EMAIL: otron.sensor@gmail.com
<http://www.e-otron.com>

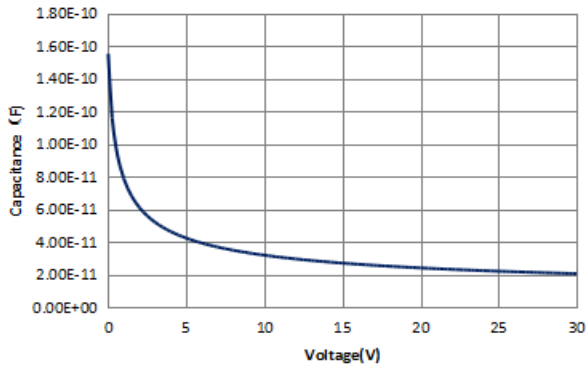
SPECTRAL RESPONSE (Ta=23°C)



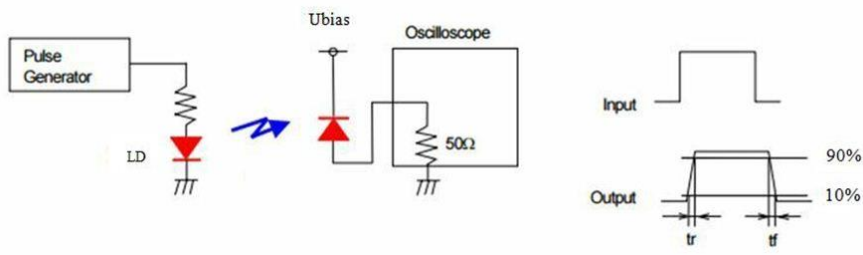
DARK CURRENT VS. REVERSE VOLTAGE (Ta=23°C)



CAPACITANCE VS. REVERSE VOLTAGE (Ta=23°C)



* Response Time Measure Circuit:



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